

SJPL-L2

Fast Recovery Diode

Jan. 2011

General Description

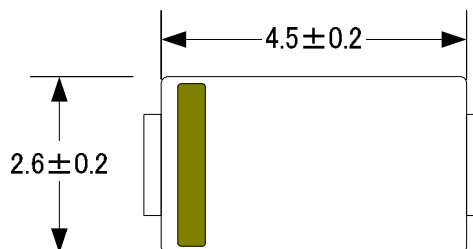
A surface mount device added to 200V_L series.

Realizes better space-saving in mounting on a printed circuit board by using a surface mount package.

Applications

- DC-DC converters
- AC adapter
- High frequency rectification circuit

Package



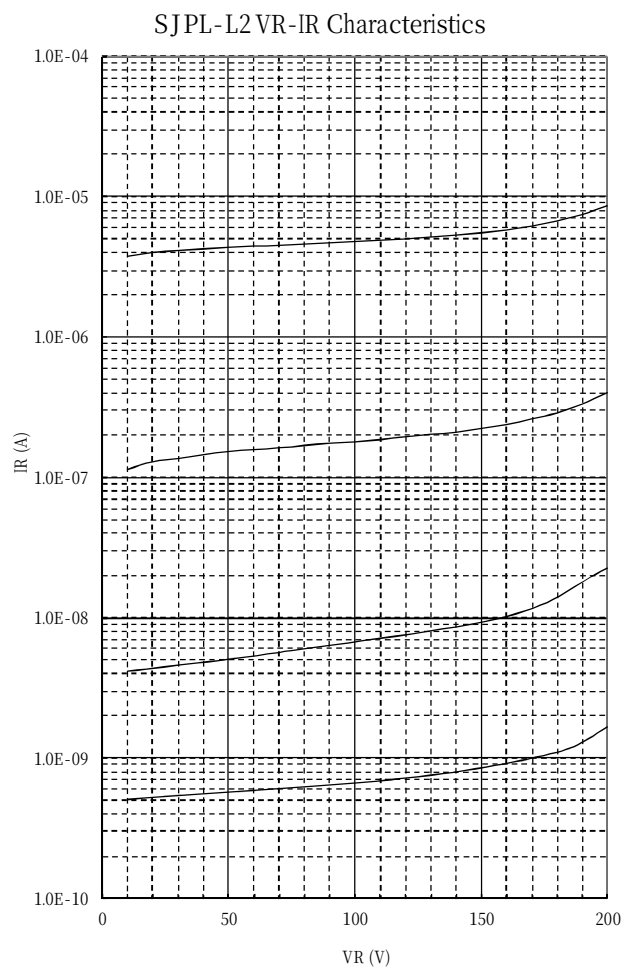
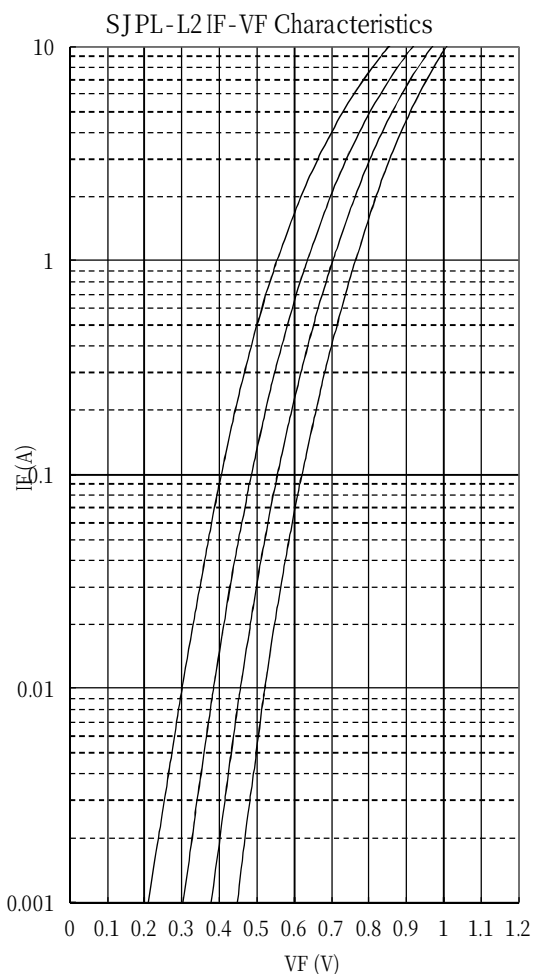
Key Specifications

Item	Unit	Rating	Conditions
V_{RM}	V	200	
V_F	V	0.98	$I_F=3.0A$
$I_{F(AV)}$	A	3.0	
t_{rr}	ns	35	100mA/200mA

Features

- Super-high speed Fast Recovery Diode
- Steady operation is possible even at the high temperature by the low leakage current.

Typical Characteristics



The information included herein is believed to be accurate and reliable. However, SANKEN ELECTRIC CO., LTD assumes no responsibility for its use ; nor for any infringements of patents or other rights of third parties that may result from its use.

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★ Absolute maximum ratings

No.	Item	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	V_{RSM}	V	200	
2	Peak Reverse Voltage	V_{RM}	V	200	
3	Average Forward Current	$I_{F(AV)}$	A	3.0	
4	Peak Surge Forward Current	I_{FSM}	A	60	Half sinewave, one shot
5	I^2t Limiting Value	I^2t	A^2s	18	$1msec \leq t \leq 10msec$
6	Junction Temperature	T_j	°C	-40~+150	
7	Storage Temperature	T_{stg}	°C	-40~+150	

★ Electrical characteristics($T_a=25^\circ C$, unless otherwise specified)

No.	Item	Symbol	Unit	Value	Conditions
1	Forward Voltage Drop	V_F	V	0.98 max.	$I_F=3.0A$
2	Reverse Leakage Current	I_R	μA	50 max.	$V_R=V_{RM}$
3	Reverse Leakage Current Under High Temperature	$H-I_R$	mA	300 max.	$V_R=V_{RM}$, $T_j=150^\circ C$
4	Reverse Recovery Time	t_{rr1}	ns	50 max.	$I_F=I_{RP}=100mA$ 90% Recovery point, $T_j=25^\circ C$
		t_{rr2}	ns	35 max.	$I_F=100mA$, $I_{RP}=200mA$ 75% Recovery point, $T_j=25^\circ C$
5	Thermal Resistance	$R_{th(j-c)}$	°C /W	20 max.	Between Junction and Lead

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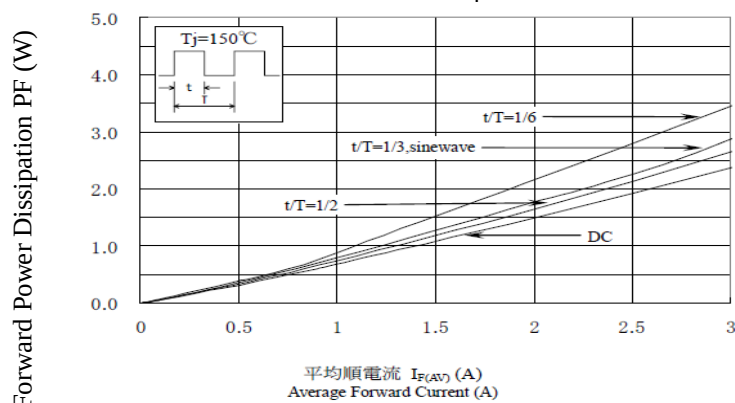
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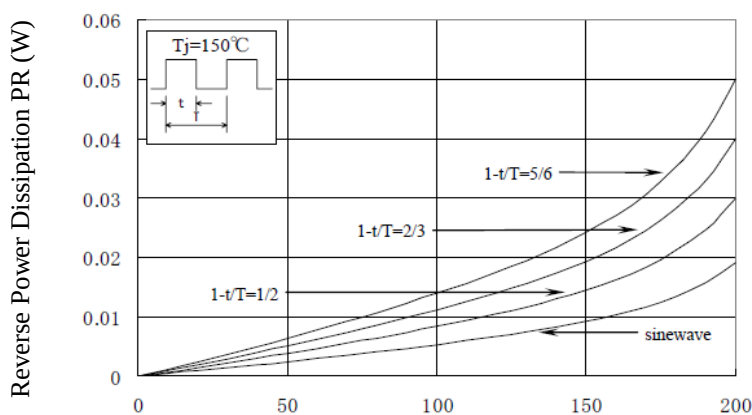
★ Characteristics

Forward Power Dissipation



Average Forward Current $I_{F(AV)}$ (A)

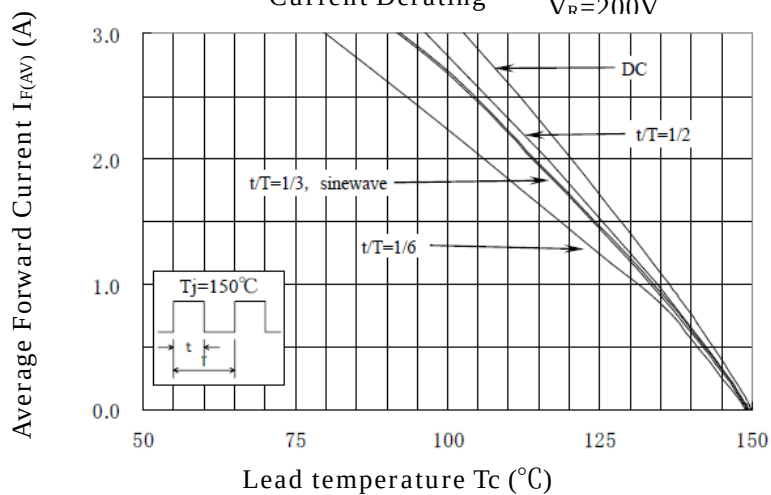
Reverse Power Dissipation



Reverse Voltage V_R (V)

Current Derating

$V_R=200\text{V}$

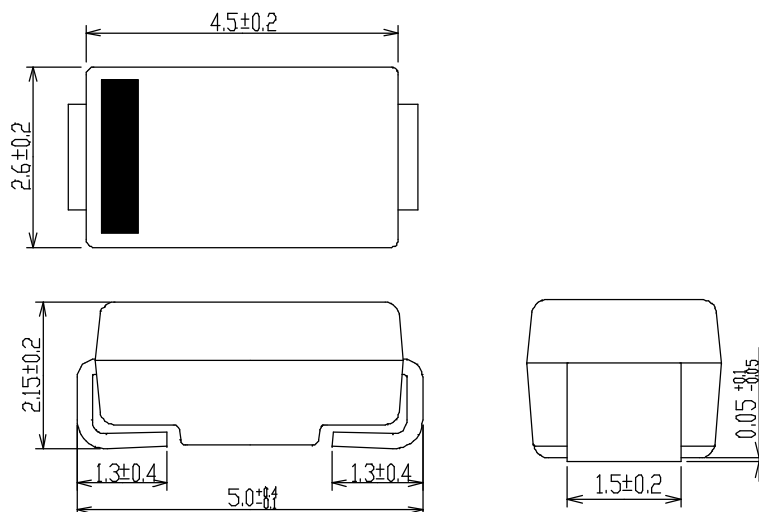


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★ Outline drawings, mm



★ Connection Diagram

